

PATENT ASSIGNMENT COVER SHEET

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EPAS ID: PAT3130015

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
INDUSTRIAL TECHNOLOGY RESEARCH INSTITUTE	11/20/2014
RECEIVING PARTY DATA	
Name:	TAIWAN SEMICONDUCTOR MANUFACTURING CO., LTD
Street Address:	NO.8, LI-HSIN ROAD. 6, SCIENCE-BASED INDUSTRIAL PARK
City:	HSIN-CHU
State/Country:	TAIWAN
Postal Code:	300-77
PROPERTY NUMBERS Total: 4	
Property Type	Number
Patent Number:	6436816
Patent Number:	6713377
Patent Number:	6660625
Patent Number:	8362454
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SIGNATURE:	/Daniel R. McClure/
DATE SIGNED:	12/03/2014
Total Attachments: 1	
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ASSIGNMENT OF U.S. PATENTS

WHEREAS, **Industrial Technology Research Institute**, having a place of business at **No.195, Sec. 4, Chung Hsing Rd., Chutung, Hsinchu,31040, Taiwan** hereinafter referred to as **ASSIGNOR**, owns the full right, title, and interest in

No	U.S. patent application No.:	Filing Date	Title:
1	09/127,463 (US6,436,816)	1998/07/31	Method of electroless plating copper on nitride barrier
2	10/156,630 (US6,713,377)	2002/05/28	Method of electroless plating copper on nitride barrier
3	10/156,635 (US6,660,625)	2002/05/28	Method of electroless plating copper on nitride barrier
4	12/334,203 (US8,362,454)	2008/12/12	Resistive random access memory having metal oxide layer with oxygen vacancies and method for fabricating the same

WHEREAS, **Taiwan Semiconductor Manufacturing Company, Ltd.** having a place of business at **No.8, Li-Hsin Rd. 6, Science-Based Industrial Park Hsin-Chu, Taiwan 300-77**, hereinafter referred to as **ASSIGNEE**, is desirous of acquiring **ASSIGNOR'S** interest in and to said invention and any U.S. provisional, continuation, continuation-in-part, divisional, reissued, and re-examined applications and patents, to be filed or issued, relating to said invention.

NOW, THEREFORE, TO ALL WHOM IT MAY CONCERN: Be it known that, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged by **ASSIGNOR**, **ASSIGNOR** has sold, assigned and transferred and does hereby sell, assign and transfer unto **ASSIGNEE**, and **ASSIGNEE'S** successors and assigns the entire right, title and interest, for the United States of America, in and to said invention and all the rights and privileges in any application and under any and all patents that may be granted in the U.S. for the invention, including but not limited to, all corresponding provisional, continuation, continuation-in-part, divisional, reissue, and reexamination applications.

INDUSTRIAL TECHNOLOGY RESEARCH INSTITUTE

By: Alex Fan

Name: Alex Fan
Title: Deputy General Director

Date: Nov. 20, 2014

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